

Notice of References CitedApplication/Control No.
09/901,109Applicant(s)/Patent Under Reexam
Droopad et al.Examiner
B. William BaumeisterArt Unit
2815

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U.S. PATENT DOCUMENTS

		Document Number Country Code-Number-Kind Code	Date MM-YYYY ¹	Name	Classification ²	
	A	5,478,653	12/1995	Guenzer	428	446
	B	5,569,953	10/1996	Kikkawa et al.	257	607
	C	5,834,362	11/1998	Miyagaki et al.	438	507
	D					
	E					
	F					
	G					
	H					
	I					
	J					
	K					
	L					
	M					

FOREIGN PATENT DOCUMENTS

		Document Number Country Code-Number-Kind Code	Date MM-YYYY ¹	Country	Name	Classification ²	
	N	JP 52-89070	7/1977	Japan	Serizawa	H01L	21/20
	O						
	P						
	Q						
	R						
	S						
	T						

NON-PATENT DOCUMENTS

		Include, as applicable: Author, Title, Date, Publisher, Edition or Volume, Pertinent Pages
	U	Kaushik et al., "Device Characteristics of Crystalline Epitaxial Oxides on Silicon;" Device Research Conference, 2000, Conference Digest 58th DRC, pp. 17-20, June 19-21, 2000.
	V	Eisenbeiser et al., Field effect transistors with SrTiO ₃ gate dielectric on Si," 6 March 2000, Applied Physics Letters, Vol. 76, No. 10, pp.1324-1326.
	W	Weiss, "Speed demon gets hooked on silicon," Science News Online, 9/15/2001.
	X	"Motorola develops new super-fast chip," USA Today, 9/4/2001.

^{*} A copy of this reference is not being furnished with this Office action. See MPEP § 707.05(a).¹ Dates in MM-YYYY format are publication dates.² Classifications may be U.S. or foreign.

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	Document Number Country Code-Number-Kind Code	Date MM-YYYY ¹	Country	Name	Classification ²
N					
O					
P					
Q					
R					
S					
T					

NON-PATENT DOCUMENTS

	Include, as applicable: Author, Title, Date, Publisher, Edition or Volume, Pertinent Pages
U	Valigra, "Motorola Lays GaAs on Si Wafer," AsiaBiz Tech, Nov. 2001.
V	"Holy Grail! Motorola claims high-yield GaAs breakthrough," Micromagazine.com (no date available).
W	
X	

^{*} A copy of this reference is not being furnished with this Office action. See MPEP § 707.05(a).¹ Dates in MM-YYYY format are publication dates.² Classifications may be U.S. or foreign.